

#### NOTES:

1. (MASTER): BUSY is output; (SLAVE): BUSY is input.

2. BUSY outputs and INT outputs are non-tri-stated push-pull.

DSC 4089/11

## Description:

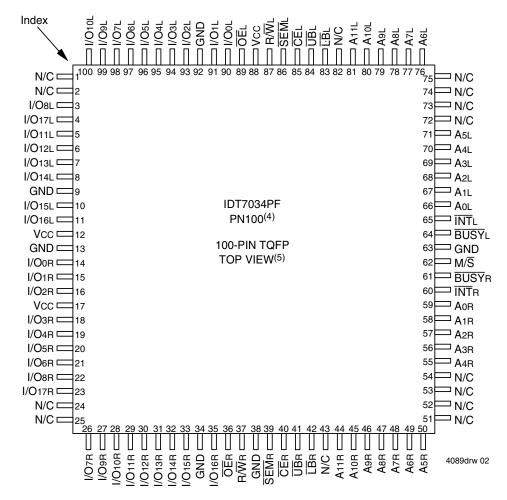
The IDT7034 is a high-speed 4K x 18 Dual-Port Static RAM. The IDT7034 is designed to be used as a stand-alone 72K-bit Dual-Port RAM or as a combination MASTER/SLAVE Dual-Port RAM for 36-bit or more word systems. Using the IDT MASTER/SLAVE Dual-Port RAM approach in 36-bit or wider memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

This device provides two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature controlled by Chip Enable ( $\overline{CE}$ ) permits the on-chip circuitry of each port to enter a very low standby power mode.

The IDT7034 utilizes a 18-bit wide data path to allow for parity at the user's option. This feature is especially useful in data communication applications.

Fabricated using CMOS high-performance technology, these devices typically operate on only 850mW of power. Low-power (L) versions offer battery backup data retention capability with typical power consumption of  $500\mu$  W from a 2V battery.

## Pin Configurations<sup>(1,2,3)</sup>



#### NOTES:

- 1. All Vcc pins must be connected to power supply
- 2. All GND pins must be connected to ground supply.
- 3. Package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

## Pin Names

Right Port	Names
ĒĒ	Chip Enable
R/WR	Read/Write Enable
ŌĒr	Output Enable
A0R - A11R	Address
I/O0r - I/O17r	Data Input/Output
<b>SEM</b> R	Semaphore Enable
ŪBR	Upper Byte Select
LBR	Lower Byte Select
ĪNTr	Interrupt Flag
<b>BUSY</b> R	Busy Flag
/\$	Master or Slave Select
сс	Power
ND	Ground
	CER   R/WR   OER   AOR - A11R   I/OOR - I/O17R   SEMR   UBR   IBR   INTR   BUSYR   /S   ccc

4089 tbl 01

## Truth Table I: Non-Contention Read/Write Control

Inputs <sup>(1)</sup>						Out	puts	
ĈĒ	R∕ <b>₩</b>	ŌĒ	ŪB	LB	SEM	I/O9-17	I/O0-8	Mode
н	Х	Х	Х	Х	Н	High-Z	High-Z	Deselected: Power-Down
х	х	х	н	н	н	High-Z	High-Z	Both Bytes Deselected
L	L	х	L	Н	н	DATAIN	High-Z	Write to Upper Byte Only
L	L	х	Н	L	н	High-Z		Write to Lower Byte Only
L	L	х	L	L	н	DATAIN		Write to Both Bytes
L	Н	L	L	Н	н	DATAOUT	High-Z	Read Upper Byte Only
L	Н	L	Н	L	н	High-Z	DATAOUT	Read Lower Byte Only
L	Н	L	L	L	Н	DATAOUT	DATAOUT	Read Both Bytes
Х	Х	Н	Х	Х	Х	High-Z	High-Z	Outputs Disabled

NOTE:

1. AoL — A11L  $\neq$  AOR — A11R

Industrial and Commercial Temperature Ranges

4089 tbl 03

4089 tbl 05

4089 tbl 06

## Truth Table II: Semaphore Read/Write Control<sup>(1)</sup>

		Inp	uts			Outputs		
CE	R∕₩	ŌĒ	ŪB	ĒΒ	SEM	I/O9-17	I/O0-8	Mode
Н	н	L	Х	Х	L	DATAOUT	DATAOUT	Read Data in Semaphore Flag
х	Н	L	Н	Н	L	DATAOUT	DATAOUT	Read Data in Semaphore Flag
н	$\uparrow$	х	Х	х	L			Write I/Oo into Semaphore Flag
х	$\uparrow$	х	Н	Н	L			Write I/Oo into Semaphore Flag
L	х	Х	L	Х	L			Not Allowed
L	х	Х	Х	L	L			Not Allowed

NOTE:

1. There are eight semaphore flags written to via I/O0 and read from I/O0 - I/O17. These eight semaphores are addressed by A0 - A2.

## Absolute Maximum Ratings<sup>(1)</sup>

Symbol	Rating	Commercial & Industrial	Unit
Vterm <sup>(2)</sup>	Terminal Voltage with Respect to GND	-0.5 to +7.0	v
TBIAS	Temperature Under Bias	-55 to +125	°C
Тѕтс	Storage Temperature	-65 to +150	°C
Ιουτ	DC Output Current	50	mA

#### NOTES:

4089 tbl 04

4089 tbl 07

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to  $\leq$  20 mA for the period over VTERM  $\geq$  Vcc + 10%.

## Capacitance $(TA = +25 \degree C, f = 1.0 \text{MHz})^{(1)}$

Symbol	Parameter	Conditions <sup>(2)</sup>	Max.	Unit
Cin	Input Capacitance	VIN = 3dV	9	pF
Соит	Output Capacitance	Vout = 3dV	10	pF

#### NOTES:

1. This parameter is determined by device characterization but is not production tested.

 3dV references the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

## Maximum Operating Temperature and Supply Voltage<sup>(1)</sup>

Grade	Ambient Temperature	GND	Vcc
Commercial	$0^{\circ}$ C to +70 $^{\circ}$ C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

NOTES:

1. This is the parameter TA. This is the "instant on" case temperature.

# Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
ViH	Input High Voltage	2.2		6.0 <sup>(2)</sup>	V
VIL	Input Low Voltage	-0.5 <sup>(1)</sup>		0.8	V

## NOTES:

1. VIL  $\geq$  -1.5V for pulse width less than 10ns.

VTERM must not exceed Vcc + 10%.

## DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (Vcc = 5.0V ± 10%)

			7034S		703		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
Lu	Input Leakage Current <sup>(1)</sup>	Vcc = 5.5V, VIN = 0V to Vcc	_	10		5	μA
Ilo	Output Leakage Current	$\overline{CE}$ = VIH, VOUT = 0V to VCC	_	10		5	μA
Vol	Output Low Voltage	Iol = 4mA		0.4	_	0.4	v
Vон	Output High Voltage	IOH = -4mA	2.4	—	2.4		V

NOTE:

1. At Vcc  $\leq$  2.0V input leakages are undefined.

4089 tbl 08

# DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(1)</sup> ( $Vcc = 5.0V \pm 10\%$ )

						4X15 Only		4X20 & Ind	
Symbol	Parameter	Test Condition	Versi	on	Typ. <sup>(2)</sup>	Max.	Typ. <sup>(2)</sup>	Max.	Unit
lcc	Dynamic Operating Current (Both Ports Active)	$\overline{CE}$ = Vil., Outputs Disabled SEM = VH	COM'L	S L	170 170	310 260	160 160	290 240	mA
		$f = fMAX^{(3)}$	IND	S L			160 160	370 320	
ISB1	Standby Current (Both Ports - TTL Level	$\label{eq:cell} \begin{split} \overline{CE}_L &= \overline{CE}_R = V \text{IH} \\ \overline{SEM}_R &= \overline{SEM}_L = V \text{IH} \\ f &= f_{MAX}^{(B)} \end{split}$	COM'L	S L	20 20	60 50	20 20	60 50	mA
	Inputs)		IND	S L			20 20	90 70	
ISB2	Standby Current (One Port - TTL Level Inputs)	$\overline{CE}_{"A"} = V_{IL}$ and $\overline{CE}_{"B"} = V_{IH}^{(5)}$ Active Port Outputs Disabled,	COM'L	S L	105 105	190 160	95 95	180 150	mA
		$\frac{f = f_{MA} x^{(3)}}{\overline{SEM}_{R}} = \overline{\overline{SEM}}_{L} = V_{I\!H}$	IND	S L			95 95	240 210	
ISB3	Full Standby Current (Both Ports - All CMOS Level	Both Ports CEL and CE <sub>R ≥</sub> Vcc - 0.2V	COM'L	S L	1.0 0.2	15 5	1.0 0.2	15 5	mA
	Inputs)		IND	S L			1.0 0.2	30 10	
ISB4	Full Standby Current (One Port - All CMOS Level Inputs)	$\overline{CE}_{A^*} \leq 0.2V$ and $\overline{CE}_{B^*} \geq V_{CC} - 0.2V^{(5)}$	COM'L	S L	100 100	170 140	90 90	155 130	mA
	" (puto)	$\label{eq:second} \begin{split} \overline{SEM} & \mathbb{R} = \overline{SEM} \mathbb{L} \geq Vcc \mbox{-} 0.2V \\ V & \mathbb{N} \geq Vcc \mbox{-} 0.2V \mbox{ or } V & \mathbb{N} \leq 0.2V \\ Active \mbox{ Port Outputs Disabled} \\ & f = f \mbox{Max}^{(3)} \end{split}$	IND	S L			90 90	225 200	

NOTES:

1. 'X' in part numbers indicates power rating (S or L)

2. Vcc = 5V, TA = +25°C, and are not production tested. lcc dc = 120mA (TYP)

3. At f = fMAX, address and I/O's are cycling at the maximum frequency read cycle of 1/tRc, and using "AC Test Conditions" of input levels of GND to 3V.

4. f = 0 means no address or control lines change.

5. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

# Data Retention Characteristics Over All Temperature Ranges (L Version Only) (Vcc = 0.2V, VHc = Vcc - 0.2V)<sup>(4)</sup>

Symbol	Parameter	Test Condi	Test Condition		Typ. <sup>(1)</sup>	Max.	Unit
Vdr	Vcc for Data Retention	Vcc = 2V		2.0	_		V
ICCDR	Data Retention Current	$\overline{CE} \ge VHC$	IND.		100	4000	μA
		VIN $\geq$ VHC or $\leq$ VLC	COM'L.	-	100	1500	
tCDR <sup>(3)</sup>	Chip Deselect to Data Retention Time	SEM ≥ VHC		0	_		ns
tR <sup>(3)</sup>	Operation Recovery Time			tRC <sup>(2)</sup>	_		ns

NOTES:

4089 tbl 10

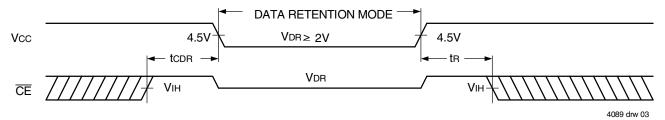
1.  $TA = +25^{\circ}C$ , Vcc = 2V, not production tested.

2. tRc = Read Cycle Time

3. This parameter is guaranteed by characterization, but is not production tested.

4. At Vcc  $\leq$  2.0V input leakages are undefined.

## Data Retention Waveform



## AC Test Conditions

Input Pulse Levels	GND to 3.0V	5V	5V
Input Rise/Fall Times	5ns Max.	$\stackrel{>}{\geq}$ 893 $\Omega$	$\stackrel{>}{\gtrsim}$ 893 $\Omega$
Input Timing Reference Levels	1.5V		
Output Reference Levels	1.5V	$\begin{array}{c c} \hline BUSY \\ \hline INT \\ 347\Omega \\ \hline 347\Omega \\ \hline \end{array} \begin{array}{c} \bullet \\ \hline \end{array} \begin{array}{c} \bullet \\ \hline \end{array} \begin{array}{c} \bullet \\ \hline \end{array} \begin{array}{c} DATAout \\ \hline \\ 347\Omega \\ \hline \end{array}$	
Output Load	Figures 1 and 2	$347\Omega \lesssim 30 \text{pF} 347\Omega$	5pF*
	4089 tbl 11		4089 drw 04

Figure 1. AC Output Test Load

Figure 2. Output Test Load (for tLz, tHz, twz, tow) \*including scope and jig.

## AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(4)</sup>

			4X15 IOnly		4X20 & Ind	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
READ CYCLE						
tRC	Read Cycle Time	15		20		ns
taa	Address Access Time	—	15		20	ns
tace	Chip Enable Access Time <sup>(3)</sup>		15		20	ns
tabe	Byte Enable Access Time <sup>(3)</sup>	-	15		20	ns
taoe	Output Enable Access Time	_	10		12	ns
toн	Output Hold from Address Change	3		3		ns
tLZ	Output Low-Z Time <sup>(1,2)</sup>	3		3		ns
tHZ	Output High-Z Time <sup>(1,2)</sup>	_	10		12	ns
tPU	Chip Enable to Power Up Time <sup>(2)</sup>	0		0		ns
tPD	Chip Disable to Power Down Time <sup>(2)</sup>	_	15		20	ns
tSOP	Semaphore Flag Update Pulse (OE or SEM)	10		10		ns
tsaa	Semaphore Address Access Time		15		20	ns
						4089 tbl 1

NOTES:

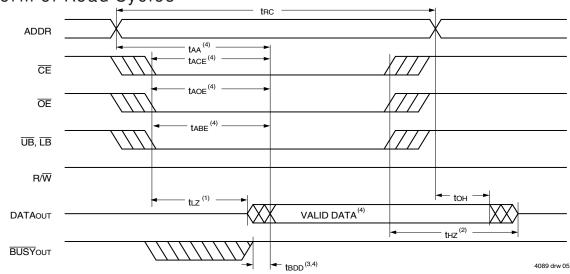
1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).

2. This parameter is guaranteed by device characterization, but is not production tested.

3. To access RAM,  $\overline{CE} = V_{IL}$ ,  $\overline{UB}$  or  $\overline{LB} = V_{IL}$ , and  $\overline{SEM} = V_{IH}$ . To access semaphore,  $\overline{CE} = V_{IH}$  or  $\overline{UB} \& \overline{LB} = V_{IH}$ , and  $\overline{SEM} = V_{IL}$ .

4. 'X' in part numbers indicates power rating (S or L).

## Waveform of Read Cycles<sup>(5)</sup>



#### NOTES:

1. Timing depends on which signal is asserted last,  $\overline{\text{OE}}$ ,  $\overline{\text{CE}}$ ,  $\overline{\text{LB}}$ , or  $\overline{\text{UB}}$ .

2. Timing depends on which signal is de-asserted first,  $\overline{\text{CE}}, \overline{\text{OE}}, \overline{\text{LB}},$  or  $\overline{\text{UB}}.$ 

3. tedd delay is required only in case where opposite port is completing a write operation to the same address location for simultaneous read operations BUSY has no relation to valid output data.

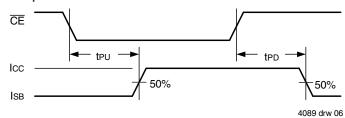
4. Start of valid data depends on which timing becomes effective last tABE, tAOE, tACE, tAA Or tBDD.

5. SEM = VIH.

Industrial and Commercial Temperature Ranges

4089 tbl 13

## Timing of Power-up Power-down



# AC Electrical Characteristics Over the Operating Temperature and Supply Voltage<sup>(5)</sup>

			4X15 I Only		4X20 & Ind		
Symbol	Parameter		Max.	Min.	Max.	Max. Unit	
WRITE CYCLE							
twc	Write Cycle Time	15	_	20	_	ns	
tew	Chip Enable to End-of-Write <sup>(3)</sup>	12		15		ns	
taw	Address Valid to End-of-Write	12		15		ns	
tas	Address Set-up Time <sup>(3)</sup>	0	_	0	_	ns	
twp	Write Pulse Width	12		15		ns	
twR	Write Recovery Time	0	_	0	_	ns	
tDW	Data Valid to End-of-Write	10		15		ns	
tHZ	Output High-Z Time <sup>(1,2)</sup>		10		12	ns	
tDH	Data Hold Time <sup>(4)</sup>	0		0		ns	
twz	Write Enable to Output in High- $Z^{(1,2)}$		10		12	ns	
tow	Output Active from End-of-Write <sup>(1,2,4)</sup>	0		0		ns	
tswrd	SEM Flag Write to Read Time	5		5		ns	
tsps	SEM Flag Contention Window	5		5		ns	

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).

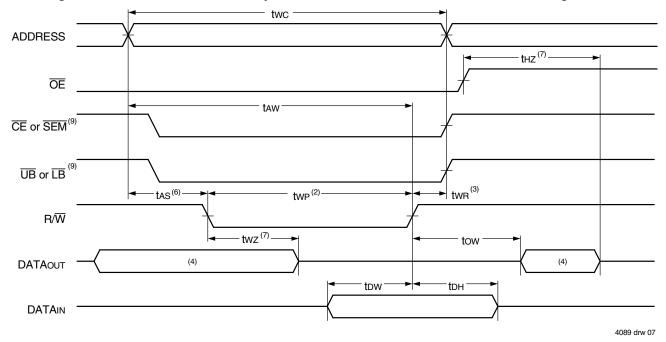
2. This parameter is guaranteed by device characterization, but is not production tested.

3. To access RAM,  $\overrightarrow{CE} = VIL$ ,  $\overrightarrow{UB}$  or  $\overrightarrow{LB} = VIL$ ,  $\overrightarrow{SEM} = VIH$ . To access semaphore,  $\overrightarrow{CE} = VIH$  or  $\overrightarrow{UB} \& \overrightarrow{LB} = VIH$ , and  $\overrightarrow{SEM} = VIL$ . Either condition must be valid for the entire tew time.

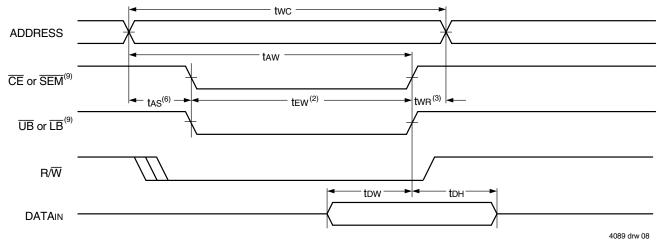
4. The specification for tDH must be met by the device supplying write data to the RAM under all operating conditions. Although tDH and tow values will vary over voltage and temperature, the actual tDH will always be smaller than the actual tow.

5. 'X' in part numbers indicates power rating (S or L).

Timing Waveform of Write Cycle No. 1, R/W Controlled Timing<sup>(1,5,8)</sup>



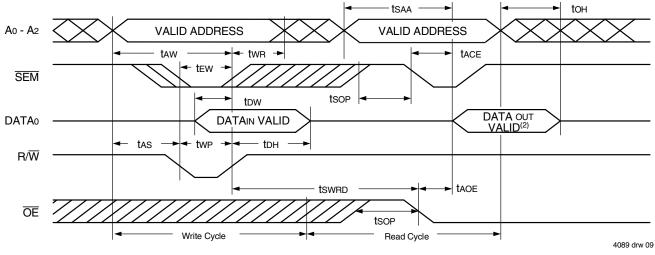
Timing Waveform of Write Cycle No. 2, **CE**, **UB**, **LB** Controlled Timing<sup>(1,5)</sup>



NOTES:

- 1. R/W or  $\overline{CE}$  or  $\overline{UB}$  &  $\overline{LB}$  must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a LOW UB or LB and a LOW CE and a LOW R/W for memory array writing cycle.
- 3. two is measured from the earlier of  $\overline{CE}$  or  $R/\overline{W}$  (or  $\overline{SEM}$  or  $R/\overline{W}$ ) going HIGH to the end-of-write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE or SEM LOW transition occurs simultaneously with or after the R/W LOW transition, the outputs remain in the high-impedance state.
- 6. Timing depends on which enable signal is asserted last,  $\overline{CE}$ ,  $R/\overline{W}$ , or byte control.
- 7. This parameter is guaranteed by device characterization, but is not production tested. Transition is measured 0mV from steady state with Output Test Load (Figure 2).
- If OE is LOW during R/W controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off and data to be placed on the bus for the required tow. If OE is HIGH during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 9. To access RAM,  $\overline{CE}$  = VIL,  $\overline{UB}$  or  $\overline{LB}$  = VIL, and  $\overline{SEM}$  = VIH. To access semaphore,  $\overline{CE}$  = VIH or  $\overline{UB}$  &  $\overline{LB}$  = VIH, and SEM = VIL. tew must be met for either condition.

Timing Waveforme of Semaphore Read After Write Timing, Either Side<sup>(1)</sup>

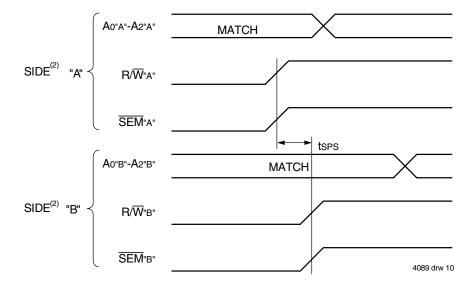


NOTE:

1.  $\overline{CE}$  = VIH or  $\overline{UB}$  &  $\overline{LB}$  = VIH for the duration of the above timing (both write and read cycle).

2. "DATAOUT VALID' represents all I/Os (I/O0-I/O17) equal to the semaphore value.

## Timing Waveform of Semaphore Write $Contention^{(1,3,4)}$



#### NOTES:

- 1. DOR = DOL = VIL,  $\overline{CE}R = \overline{CE}L = VIH$ , or both  $\overline{UB} \& \overline{LB} = VIH$ .
- 2. All timing is the same for left and right port. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 3. This parameter is measured from R/W"A" or SEM"A" going HIGH to R/W"B" or SEM"B" going HIGH.
- 4. If tsps is not satisfied, there is no guarantee which side will obtain the semaphore flag.

# AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(6)</sup>

			4X15 IOnly		4X20 & Ind	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
BUSY TIMING	G (M/S=VIH)					
tBAA	BUSY Access Time from Address Match		15		20	ns
tBDA	BUSY Disable Time from Address Not Matched		15		20	ns
tBAC	BUSY Access Time from Chip Enable Low		15		20	ns
tBDC	BUSY Access Time from Chip Enable High		15		17	ns
taps	Arbitration Priority Set-up Time <sup>(2)</sup>	5		5		ns
tBDD	BUSY Disable to Valid Data <sup>(3)</sup>		18		30	ns
twн	Write Hold After BUSY <sup>(5)</sup>	12		15		ns
BUSY TIMING	$\overline{\mathbf{G}}$ (M/ $\overline{\mathbf{S}}$ =VIL)	-				-
twв	BUSY Input to Write <sup>(4)</sup>	0		0		ns
twн	Write Hold After BUSY <sup>(5)</sup>	12		15		ns
PORT-TO-PO	RT DELAY TIMING					
twdd	Write Pulse to Data Delay <sup>(1)</sup>		30		45	ns
tDDD	Write Data Valid to Read Data Delay <sup>(1)</sup>		25		30	ns
		•		•	•	4089 tbl 1

NOTES:

1. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Read With BUSY (M/S = VIH)" or "Timing Waveform of Write With Port-To-Port Delay (M/S = VIH)".

2. To ensure that the earlier of the two ports wins.

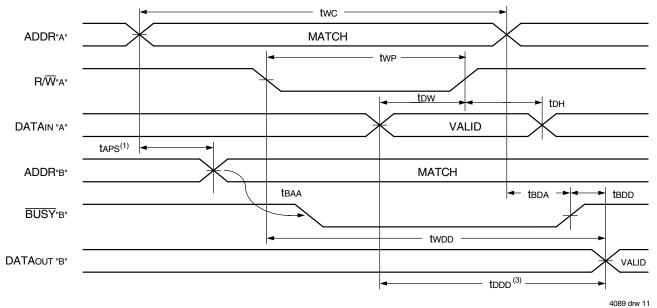
3. tBDD is a calculated parameter and is the greater of Ons, twDD - twP (actual) or tDDD - tDw (actual).

4. To ensure that the write cycle is inhibited on Port "B" during contention with Port "A".

5. To ensure that a write cycle is completed on Port "B" after contention with Port "A".

6. 'X' in part numbers indicates power rating (S or L).

## Timing Waveform of Write Port-to-Port Read and $\overline{\text{BUSY}}^{(2,5)}$ (M/ $\overline{\text{S}}$ = VIH)<sup>(4)</sup>

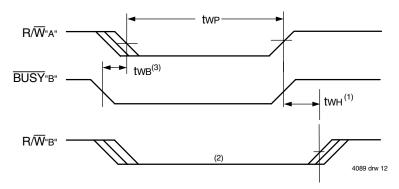


NOTES:

- 1. To ensure that the earlier of the two ports wins. tAPS is ignored for  $M/\overline{S} = VIL$  (slave).
- 2.  $\overline{CE}L = \overline{CE}R = VIL.$
- 3.  $\overline{OE} = V_{IL}$  for the reading port.
- 4. If  $M/\overline{S} = VIL$  (SLAVE) then  $\overline{BUSY}$  is an input.  $\overline{BUSY}^{"A"} = VIL$  and  $\overline{BUSY}^{"B"} =$  'don't care'

5. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the opposite Port from Port "A".

## Timing Waveform of Write with **BUSY**



NOTES:

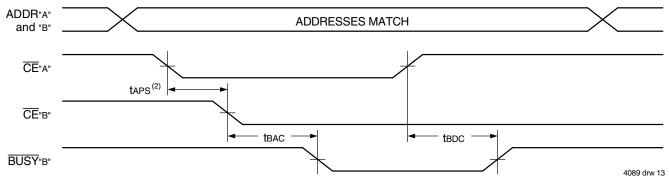
1. twn must be met for both  $\overline{\text{BUSY}}$  input (slave) output master.

2. BUSY is asserted on port "B" Blocking R/W"B", until BUSY"B" goes HIGH.

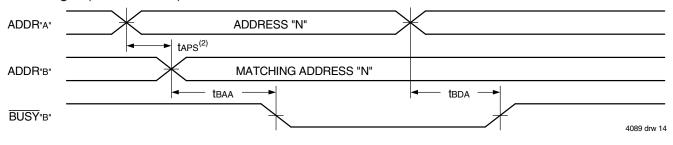
3. twb is only for the 'Slave' Version.

Industrial and Commercial Temperature Range

## Waveform of **BUSY** Arbitration Controlled by $\overline{CE}$ Timing<sup>(1)</sup> (M/ $\overline{S}$ = VIH)



## Waveform of **BUSY** Arbitration Cycle Controlled by Address Match Timing<sup>(1)</sup>(M/S = VIH)



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from "A".

2. If tAPS is not satisfied, the BUSY signal will be asserted on one side or another but there is no guarantee on which side BUSY will be asserted.

## AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(1)</sup>

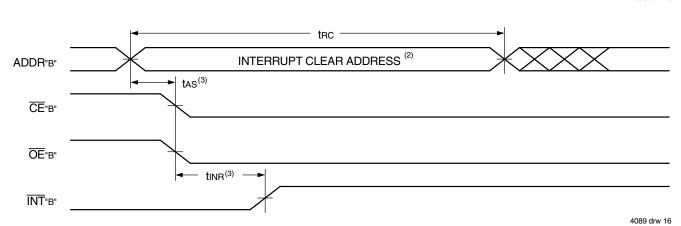
		7034X15 Com'l Only		7034X20 Com'l & Ind			
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit	
INTERRUP	T TIMING						
tas	Address Set-up Time	0	_	0	_	ns	
twr	Write Recovery Time	0	_	0		ns	
tins	Interrupt Set Time		15	_	20	ns	
tinr	Interrupt Reset Time		15	_	20	ns	
					4	089 tbl 15	

NOTES:

1. 'X' in part numbers indicates power rating (S or L).

# Waveform of Interrupt Timing<sup>(1)</sup> ADDR<sup>\*</sup>A<sup>\*\*</sup> $\xrightarrow{\text{twc}} \underbrace{\text{twc}}_{\text{tas}^{(3)}} \underbrace{\text{twc}}_{\text{tas}^{(3)}} \underbrace{\text{twc}}_{\text{twr}^{(4)}} \underbrace{\text{twr}^{(4)}}_{\text{twr}^{(4)}} \underbrace{\text{twr}^{(4)}}_{\text{t$

4089 drw 15



NOTES:

ĪNT"B"

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from "A".

 $t_{\rm INS}^{\,(3)}$ 

2. See Interrupt Flag Truth Table III.

- 3. Timing depends on which enable signal ( $\overline{CE}$  or  $R/\overline{W}$ ) is asserted last.
- 4. Timing depends on which enable signal  $(\overline{CE} \text{ or } R/\overline{W})$  is de-asserted first.

Left Port					Right Port					
R∕ <b>W</b> ∟	CE∟	ŌĒ∟	A0L-A11L	ĪNT∟	R∕ <b>₩</b> R	<b>CE</b> R	<b>OE</b> R	A0R-A11R	<b>İNT</b> R	Function
L	L	х	FFF	х	х	х	х	х	L <sup>(2)</sup>	Set Right INTR Flag
х	х	х	х	х	х	L	L	FFF	H <sup>(3)</sup>	Reset Right INTR Flag
х	х	х	х	L <sup>(3)</sup>	L	L	х	FFE	х	Set Left INTL Flag
х	L	L	FFE	H <sup>(2)</sup>	х	х	х	х	х	Reset Left INT∟ Flag

## Truth Table III — Interrupt Flag<sup>(1)</sup>

NOTES:

1. Assumes  $\overline{BUSY}_{L} = \overline{BUSY}_{R} = V_{IH}$ .

2. If  $\overline{BUSY}_{L} = V_{IL}$ , then no change.

3. If  $\overline{BUSY}_{R} = VIL$ , then no change.

4. INTR and INTL must be initialized at power-up.

# Truth Table IV — Address **BUSY** Arbitration

	In	puts	Out	puts	
CE∟	<b>CE</b> R	Aol-A11L Aor-A11r	BUSTL <sup>(1)</sup>	<b>BUSY</b> R <sup>(1)</sup>	Function
Х	х	NO MATCH	н	Н	Normal
Н	х	MATCH	н	Н	Normal
х	н	MATCH	н	н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit <sup>(3)</sup>

#### NOTES:

4089 tbl 17

1. Pins BUSYL and BUSYR are both outputs when the part is configured as a master. BUSY are inputs when configured as a slave. BUSYx outputs on the IDT7034 are push pull, not open drain outputs. On slaves the BUSY asserted internally inhibits write.

 "L" if the inputs to the opposite port were stable prior to the address and enable inputs of this port. "H" if the inputs to the opposite port became stable after the address and enable inputs of this port. If tAPS is not met, either BUSYL or BUSYR = LOW will result. BUSYL and BUSYR outputs cannot be LOW simultaneously.

3. Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

## Truth Table V — Example of Semaphore Procurement Sequence<sup>(1,2,3)</sup>

Functions	Do - D17 Left	Do - D17 Right	Status
No Action	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Right Port Writes "0" to Semaphore	0	1	No change. Right side has no write access to semaphore
Left Port Writes "1" to Semaphore	1	0	Right port obtains semaphore token
Left Port Writes "0" to Semaphore	1	0	No change. Left port has no write access to semaphore
Right Port Writes "1" to Semaphore	0	1	Left port obtains semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free
Right Port Writes "0" to Semaphore	1	0	Right port has semaphore token
Right Port Writes "1" to Semaphore	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free

NOTES:

1. This table denotes a sequence of events for only one of the eight semaphores on the IDT7034.

2. There are eight semaphore flags written to via I/Oo and read from all I/O's. These eight semaphores are addressed by Ao - A2.

3.  $\overline{CE} = V_{IH}$ ,  $\overline{SEM} = V_{IL}$  to access the semaphores. Refer to the semaphore Read/Write Control Truth Table.

#### FUNCTIONAL DESCRIPTION

The IDT7034 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT7034 has an automatic power down feature controlled by CE. The CE controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected (CE HIGH). When a port is enabled, access to the entire memory array is permitted.

#### **INTERRUPTS**

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag ( $\overline{INT}L$ ) is asserted when the right port writes to memory location FFE (HEX), where a write is defined as the  $\overline{CE}R = R/WR = V_{IL}$  per Truth Table III. The left port clears the interrupt by an address location FFE access when  $\overline{CE}L = \overline{OE}L = V_{IL}$ , R/WL is a "don't care". Likewise, the right port interrupt flag ( $\overline{INT}R$ ) is asserted when the left port writes to memory location FFF (HEX) and to clear the interrupt flag ( $\overline{INT}R$ ), the right port must access the memory location FFF. The message (18 bits) at FFE or FFF is user-defined, since it is an addressable SRAM location. If the interrupt function is not used, address locations FFE and FFF are not used as mail boxes, but as part of the random access memory. Refer to Table III for the interrupt operation.

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#### **BUSY LOGIC**

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "busy". The  $\overline{BUSY}$  pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a  $\overline{BUSY}$  indication, the write signal is gated internally to prevent the write from proceeding.

The use of  $\overline{BUSY}$  logic is not required or desirable for all applications. In some cases it may be useful to logically OR the  $\overline{BUSY}$  outputs together and use any  $\overline{BUSY}$  indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of  $\overline{BUSY}$  logic is not desirable, the  $\overline{BUSY}$  logic can be disabled by placing the part in slave mode with the M/S pin. Once in slave mode the  $\overline{BUSY}$  pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the  $\overline{BUSY}$  pins HIGH. If desired, unintended write operations can be prevented to a port by tying the  $\overline{BUSY}$  pin for that port LOW.

The  $\overline{BUSY}$  outputs on the IDT7034 RAM in master mode, are pushpull type outputs and do not require pull up resistors to operate. If these RAMs are being expanded in depth, then the  $\overline{BUSY}$  indication for the resulting array requires the use of an external AND gate.

## WIDTH EXPANSION WITH BUSY LOGIC MASTER/SLAVE ARRAYS

When expanding an IDT7034 RAM array in width while using  $\overline{BUSY}$  logic, one master part is used to decide which side of the RAM array will receive a  $\overline{BUSY}$  indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the  $\overline{BUSY}$  signal as a write inhibit signal. Thus on the IDT7034 RAM the  $\overline{BUSY}$  pin is an output if the part is used as a master ( $M/\overline{S}$  pin = VIH), and the  $\overline{BUSY}$  pin is an input if the part used as a slave ( $M/\overline{S}$  pin = VIL) as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating  $\overline{BUSY}$  on one side of the array and another master indicating  $\overline{BUSY}$  on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The BUSY arbitration, on a master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a  $\overline{\text{BUSY}}$  flag to be output from the master before the actual write pulse can be initiated with either the  $R/\overline{W}$  signal or the byte enables. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

#### SEMAPHORES

The IDT7034 is an extremely fast Dual-Port 4K x 18 CMOS Static RAM with an additional 8 address locations dedicated to binary semaphore flags. These flags allow either processor on the left or right side of the Dual-Port RAM to claim a privilege over the other processor for functions defined by the system designer's software. As an example, the semaphore can be used by one processor to inhibit the

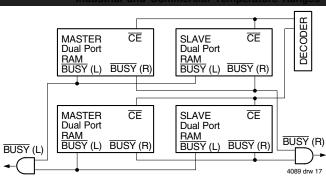


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT7034 RAMs.

other from accessing a portion of the Dual-Port RAM or any other shared resource.

The Dual-Port RAM features a fast access time, and both ports are completely independent of each other. This means that the activity on the left port in no way slows the access time of the right port. Both ports are identical in function to standard CMOS Static RAM and can be read from, or written to, at the same time with the only possible conflict arising from the simultaneous writing of, or a simultaneous READ/WRITE of, a non-semaphore location. Semaphores are protected against such ambiguous situations and may be used by the system program to avoid any conflicts in the non-semaphore portion of the Dual-Port RAM. These devices have an automatic power-down feature controlled by  $\overline{CE}$ , the Dual-Port RAM enable, and  $\overline{SEM}$ , the semaphore enable. The  $\overline{CE}$  and  $\overline{SEM}$  pins control on-chip power down circuitry that permits the respective port to go into standby mode when not selected. This is the condition which is shown in Truth Table I where  $\overline{CE}$  and  $\overline{SEM}$  are both HIGH.

Systems which can best use the IDT7034 contain multiple processors or controllers and are typically very high-speed systems which are software controlled or software intensive. These systems can benefit from a performance increase offered by the IDT7034's hardware semaphores, which provide a lockout mechanism without requiring complex programming.

Software handshaking between processors offers the maximum in system flexibility by permitting shared resources to be allocated in varying configurations. The IDT7034 does not use its semaphore flags to control any resources through hardware, thus allowing the system designer total flexibility in system architecture.

An advantage of using semaphores rather than the more common methods of hardware arbitration is that wait states are never incurred in either processor. This can prove to be a major advantage in very high-speed systems.

#### HOW THE SEMAPHORE FLAGS WORK

The semaphore logic is a set of eight latches which are independent of the Dual-Port RAM. These latches can be used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphores provide a hardware assist for a use assignment method called "Token Passing Allocation." In this method,

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the state of a semaphore latch is used as a token indicating that shared resource is in use. If the left processor wants to use this resource, it requests the token by setting the latch. This processor then verifies its success in setting the latch by reading it. If it was successful, it proceeds to assume control over the shared resource. If it was not successful in setting the latch, it determines that the right side processor has set the latch first, has the token and is using the shared resource. The left processor can then either repeatedly request that semaphore's status or remove its request for that semaphore to perform another task and occasionally attempt again to gain control of the token via the set and test sequence. Once the right side has relinquished the token, the left side should succeed in gaining control.

The semaphore flags are active LOW. A token is requested by writing a zero into a semaphore latch and is released when the same side writes a one to that latch.

The eight semaphore flags reside within the IDT7034 in a separate memory space from the Dual-Port RAM. This address space is accessed by placing a LOW input on the SEM pin (which acts as a chip select for the semaphore flags) and using the other control pins (Address,  $\overrightarrow{OE}$ , and  $\overrightarrow{R/W}$ ) as they would be used in accessing a standard Static RAM. Each of the flags has a unique address which can be accessed by either side through address pins A0 – A2. When accessing the semaphores, none of the other address pins has any effect.

When writing to a semaphore, only data pin Do is used. If a LOW level is written into an unused semaphore location, that flag will be set to a zero on that side and a one on the other side (see Table V). That semaphore can now only be modified by the side showing the zero. When a one is written into the same location from the same side, the flag will be set to a one for both sides (unless a semaphore request from the other side is pending) and then can be written to by both sides. The fact that the side which is able to write a zero into a semaphore subsequently locks out writes from the other side is what makes semaphore flags useful in interprocessor communications. (A thorough discussion on the use of this feature follows shortly.) A zero written into the same location from the other side will be stored in the semaphore request latch for that side until the semaphore is freed by the first side.

When a semaphore flag is read, its value is spread into all data bits so that a flag that is a one reads as a one in all data bits and a flag containing a zero reads as all zeros. The read value is latched into one side's output register when that side's semaphore select ( $\overline{SEM}$ ) and output enable ( $\overline{OE}$ ) signals go active. This serves to disallow the semaphore from changing state in the middle of a read cycle due to a write cycle from the other side. Because of this latch, a repeated read of a semaphore in a test loop must cause either signal ( $\overline{SEM}$  or  $\overline{OE}$ ) to go inactive or the output will never change.

A sequence WRITE/READ must be used by the semaphore in order to guarantee that no system level contention will occur. A processor requests access to shared resources by attempting to write a zero into a semaphore location. If the semaphore is already in use, the semaphore request latch will contain a zero, yet the semaphore flag will appear as one, a fact which the processor will verify by the subsequent read (see Table V). As an example, assume a processor writes a zero to the left port at a free semaphore location. On a subsequent read, the processor will verify that it has written successfully to that location and will assume control over the resource in question. Meanwhile, if a processor on the right side attempts to write a zero to the same semaphore flag it will fail, as will be verified by the fact that a one will be read from that semaphore on the right side during subsequent read. Had a sequence of READ/WRITE been used instead, system contention problems could have occurred during the gap between the read and write cycles.

It is important to note that a failed semaphore request must be followed by either repeated reads or by writing a one into the same location. The reason for this is easily understood by looking at the simple logic diagram of the semaphore flag in Figure 4. Two semaphore request latches feed into a semaphore flag. Whichever latch is first to present a zero to the semaphore flag will force its side of the semaphore flag LOW and the other side HIGH. This condition will continue until a one is written to the same semaphore request latch. Should the other side's semaphore request latch have been written to a zero in the meantime, the semaphore flag will flip over to the other side as soon as a one is written into the first side's request latch. The second side's flag will now stay LOW until its semaphore request latch is written to a one. From this it is easy to understand that, if a semaphore is requested and the processor which requested it no longer needs the resource, the entire system can hang up until a one is written into that semaphore request latch.

The critical case of semaphore timing is when both sides request a single token by attempting to write a zero into it at the same time. The semaphore logic is specially designed to resolve this problem. If simultaneous requests are made, the logic guarantees that only one side receives the token. If one side is earlier than the other in making the request, the first side to make the request will receive the token. If both requests arrive at the same time, the assignment will be arbitrarily made to one port or the other.

One caution that should be noted when using semaphores is that semaphores alone do not guarantee that access to a resource is secure. As with any powerful programming technique, if semaphores are misused or misinterpreted, a software error can easily happen.

Initialization of the semaphores is not automatic and must be handled via the initialization program at power-up. Since any semaphore request flag which contains a zero must be reset to a one, all semaphores on both sides should have a one written into them at initialization from both sides to assure that they will be free when needed.

#### USING SEMAPHORES—SOME EXAMPLES

Perhaps the simplest application of semaphores is their application as resource markers for the IDT7034's Dual-Port RAM. Say the 4K x 18 RAM was to be divided into two 2K x 18 blocks which were to be dedicated at any one time to servicing either the left or right port. Semaphore 0 could be used to indicate the side which would control the lower section of memory, and Semaphore 1 could be defined as the indicator for the upper section of memory.

To take a resource, in this example the lower 2K of Dual-Port RAM, the processor on the left port could write and then read a zero in to Semaphore 0. If this task was successfully completed (a zero was read back rather than a one), the left processor would assume control of the

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lower 2K. Meanwhile the right processor was attempting to gain control of the resource after the left processor, it would read back a one in response to the zero it had attempted to write into Semaphore 0. At this point, the software could choose to try and gain control of the second 2K section by writing, then reading a zero into Semaphore 1. If it succeeded in gaining control, it would lock out the left side.

Once the left side was finished with its task, it would write a one to Semaphore 0 and may then try to gain access to Semaphore 1. If Semaphore 1 was still occupied by the right side, the left side could undo its semaphore request and perform other tasks until it was able to write, then read a zero into Semaphore 1. If the right processor performs a similar task with Semaphore 0, this protocol would allow the two processors to swap 2K blocks of Dual-Port RAM with each other.

The blocks do not have to be any particular size and can even be variable, depending upon the complexity of the software using the semaphore flags. All eight semaphores could be used to divide the Dual-Port RAM or other shared resources into eight parts. Semaphores can even be assigned different meanings on different sides rather than being given a common meaning as was shown in the example above.

Semaphores are a useful form of arbitration in systems like disk interfaces where the CPU must be locked out of a section of memory

during a transfer and the I/O device cannot tolerate any wait states. With the use of semaphores, once the two devices has determined which memory area was "off-limits" to the CPU, both the CPU and the I/O devices could access their assigned portions of memory continuously without any wait states.

Semaphores are also useful in applications where no memory "WAIT" state is available on one or both sides. Once a semaphore handshake has been performed, both processors can access their assigned RAM segments at full speed.

Another application is in the area of complex data structures. In this case, block arbitration is very important. For this application one processor may be responsible for building and updating a data structure. The other processor then reads and interprets that data structure. If the interpreting processor reads an incomplete data structure, a major error condition may exist. Therefore, some sort of arbitration must be used between the two different processors. The building processor arbitrates for the block, locks it and then is able to go in and update the data structure. When the update is completed, the data structure block is released. This allows the interpreting processor to come back and read the complete data structure, thereby guaranteeing a consistent data structure.

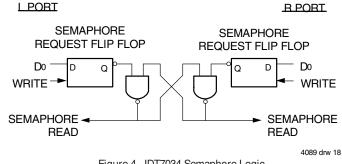
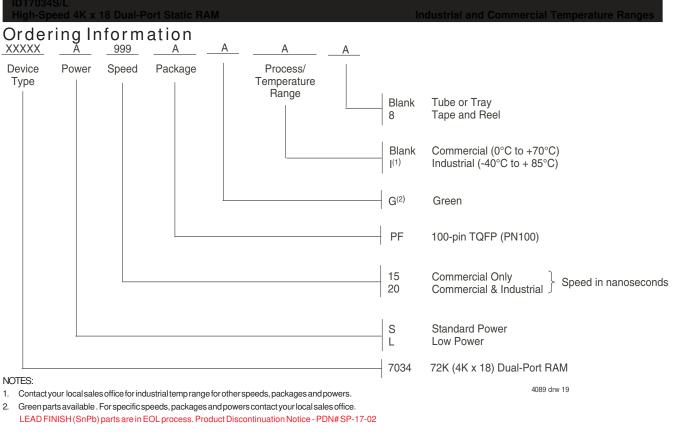


Figure 4. IDT7034 Semaphore Logic



## Datasheet Document History

12/03/98:	Initiated datasheet document history
	Converted to new format
	Cosmetic typographical corrections
	Added additional notes to pin configurations
05/19/99:	Page 9 Fixed typographical error
06/03/99:	Changed drawing format
	Page 1 Corrected DSC number
09/01/99:	Removed Preliminary
10/04/99:	Removed Industrial Temperature Ranges and removed corresponding notes
11/10/99:	Replaced IDT logo
05/22/00:	Page 4 Increased storage temperature parameter
	Clarified TA parameter
	Page 5 DC Electrical parameters-changed wording from "open" to "disabled"
	Changed ±500mV to 0mV in notes
01/29/09:	Page 19 Removed "IDT" from orderable part number
06/05/15:	Page 1 Added Green availability to Features
	Page 2 Removed IDT in reference to fabrication
	Page 2 & 19 The package code for PN100-1 changed to PN100 to match the standard package codes
	Page 19 Added Green and T&R indicators and the correlating footnotes to Ordering Information
05/29/18:	Product Discontinuation Notice - PDN# SP-17-02
	Last time buy expires June 15, 2018
03/17/22:	7034 Datasheet changed to Obsolete Status



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